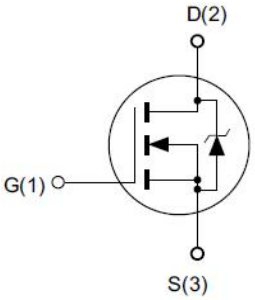
MU6888D

N-Channel Enhancement Mode MOSFET

Features

- 68V, 88A, $R_{DS(on)}$(Typ.) = 6.0mΩ@V_{GS} = 10V
- Excellent $R_{DS(on)}$ and Low Gate Charge
- 100% E_{AS} Guaranteed
- Halogen-free; RoHS-compliant



Application

- Load Switch
- PWM Application
- Power Management

Absolute Maximum Ratings T_c = 25°C unless otherwise noted

Symbol	Parameter		Rating	Unit
V_{DS}	Drain-Source Voltage [a]		68	V
V_{GS}	Gate-Source Voltage		±20	
I_D	Drain Current-Continuous	T_C = 25°C	88	A
		T_C = 100°C	54	
I_{DM}	Drain Current-Pulsed [b]		320	
P_D	Power Dissipation, T_C = 25°C		109	W
E_{AS}	Single Pulsed Avalanche Energy [c]		306	mJ
T_J, T_{STG}	Operating and Store Temperature Range		150, -55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.15	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

Electrical Characteristics T_J = 25°C unless otherwise noted

■ **Off Characteristics**

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	68	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 68V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Forward Gate Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance [d]	V_{GS} = 10V, I_D = 40A	-	6.0	7.8	mΩ
		V_{GS} = 6.0V, I_D = 30A	-	8.5	11	

■ Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
R_G	Gate Resistance	V_{DS} = V_{GS} = 0V, f = 1.0MHz	-	2.0	-	Ω
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	-	3601	-	pF
C_{oss}	Output Capacitance		-	318	-	
C_{rss}	Reverse Transfer Capacitance		-	299	-	

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 35V, V_{GS} = 10V, I_D = 40A, R_{GEN} = 4.7Ω	-	20	-	ns
t_r	Turn-On Rise Time		-	51	-	
$t_{d(off)}$	Turn-Off Delay Time		-	50	-	
t_f	Turn-Off Fall Time		-	22	-	
Q_g	Total Gate Charge	V_{DS} = 35V, V_{GS} = 0 to 10V, I_D = 40A	-	75	-	nC
Q_{gs}	Gate-Source Charge		-	26	-	
Q_{gd}	Gate-Drain Charge		-	20	-	

■ Drain-Source Diode Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
I_S	Drain-Source Diode Forward Continuous Current	V_G = V_D = 0V, Force Current	-	-	88	A
I_{SM}	Maximum Pulsed Current		-	-	320	
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0V, I_S = 30A	-	-	1.1	V
T_{rr}	Body Diode Reverse Recovery Time	I_F = 20A, dI_F/dt = 100A/μs	-	23	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F = 20A, dI_F/dt = 100A/μs	-	16	-	nC

Notes:

a. T_J = +25 ℃ to +150 ℃.

b. Repetitive rating: pulse width limited by maximum junction temperature.

c. L = 0.5mH, V_{DD} = 25V, I_{AS} = 35A, R_G = 25Ω Starting T_J = 25 ℃.

d. Pulse width ≦ 300μs; duty cycle ≦ 0.5%.

■ Characteristic Curve

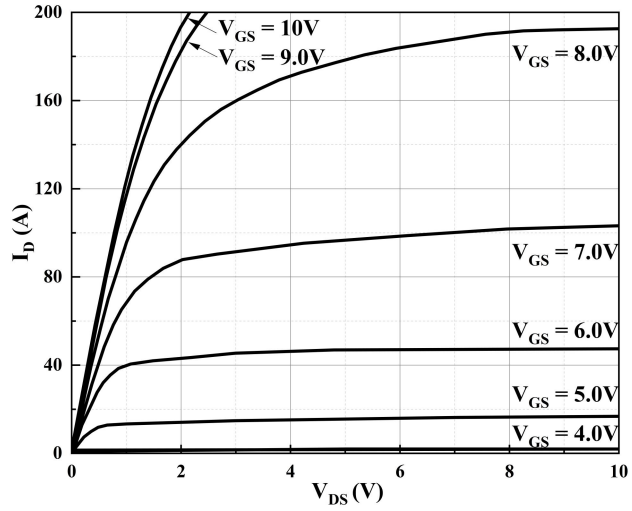


Figure 1. Typical Output Characteristics

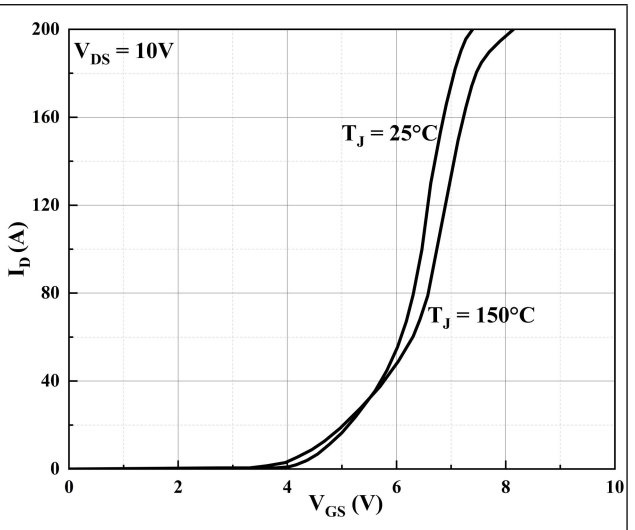


Figure 2. Typical Transfer Characteristics

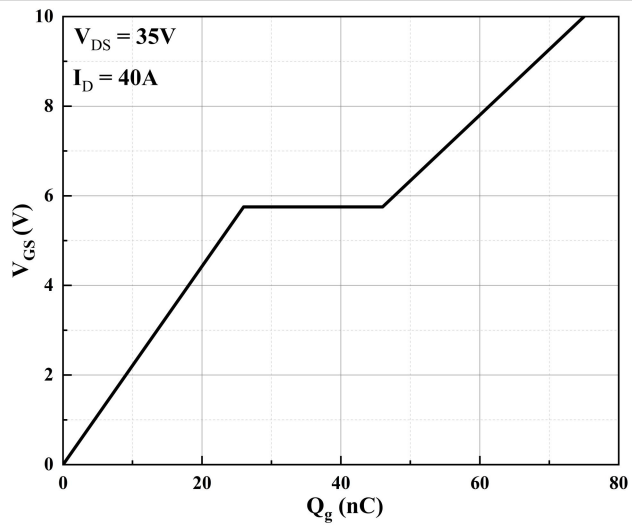


Figure 3. Typical Gate Charge

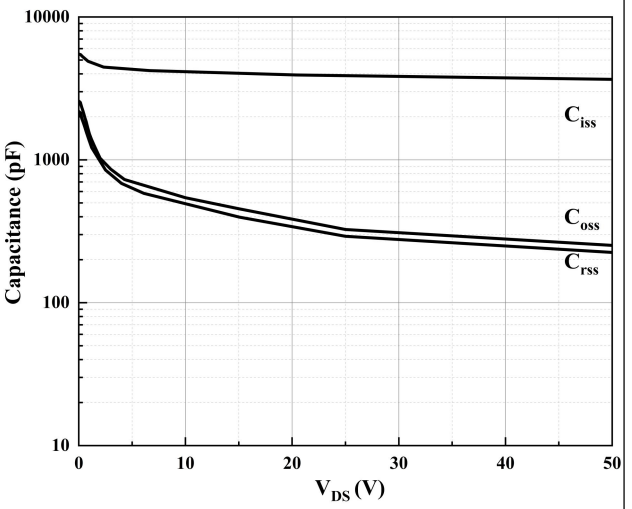


Figure 4. Typical Capacitance

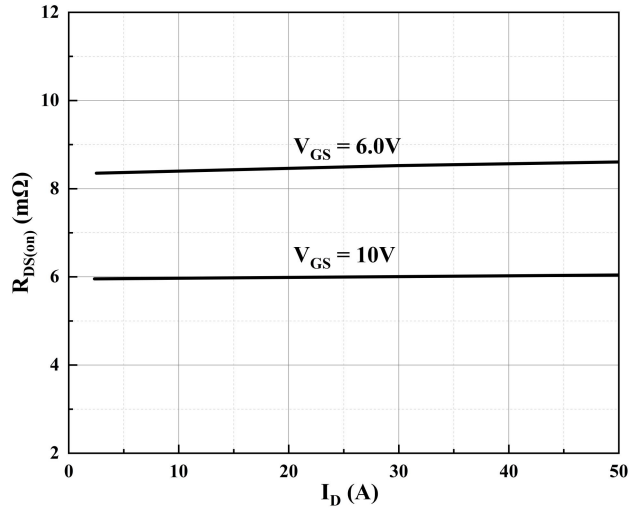


Figure 5. Static Drain-Source On-Resistance vs. Drain Current

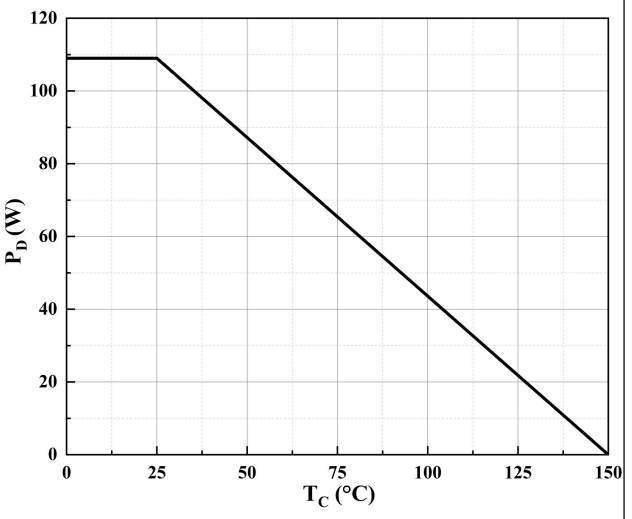


Figure 6. Power Dissipation vs. Case Temperature

■ Characteristic Curve

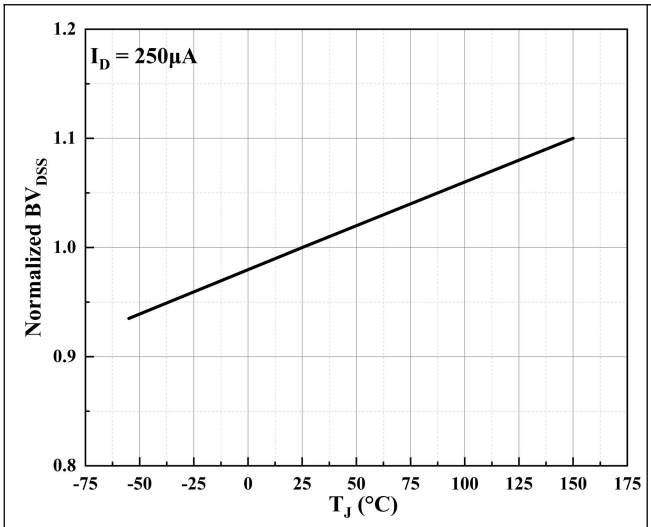


Figure 7. Normalized Breakdown Voltage vs. Junction Temperature

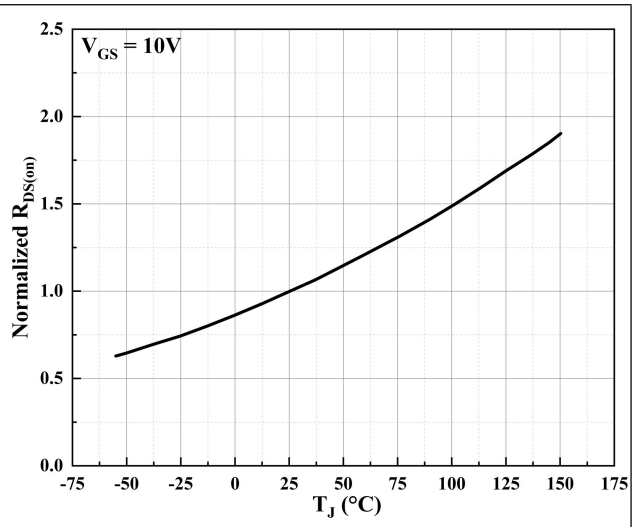


Figure 8. Normalized Static Drain-Source On-Resistance vs. Junction Temperature

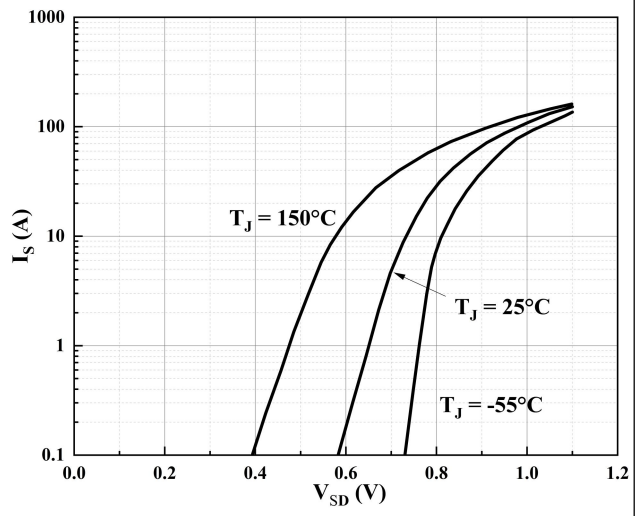


Figure 9. Body Diode Characteristics

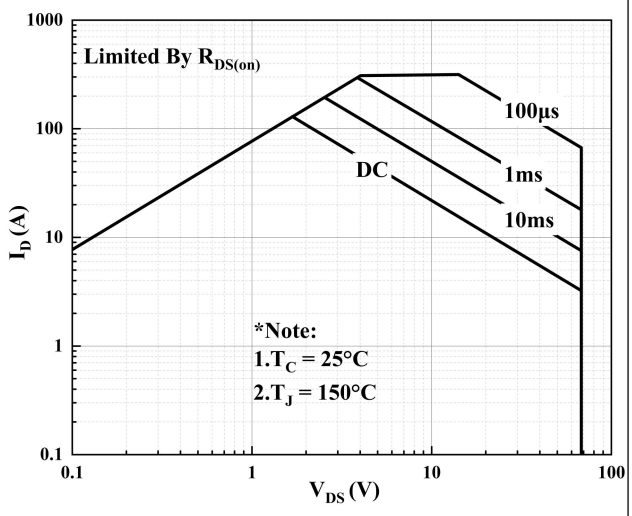


Figure 10. Safe Operating Area

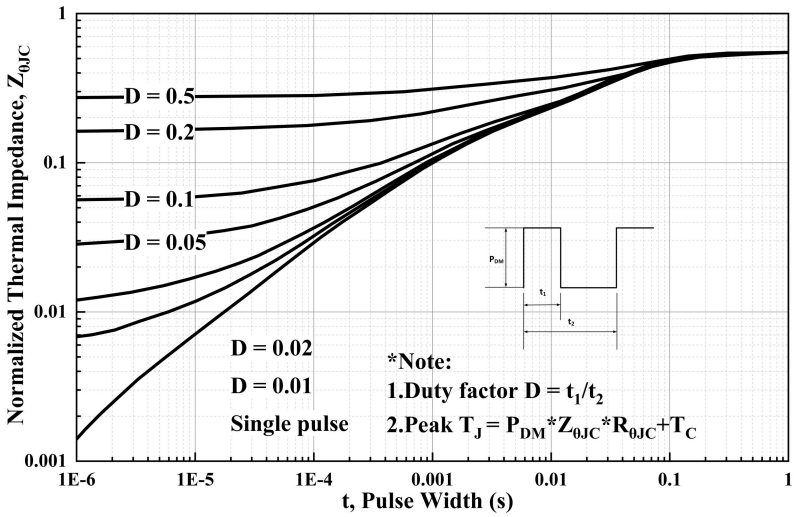
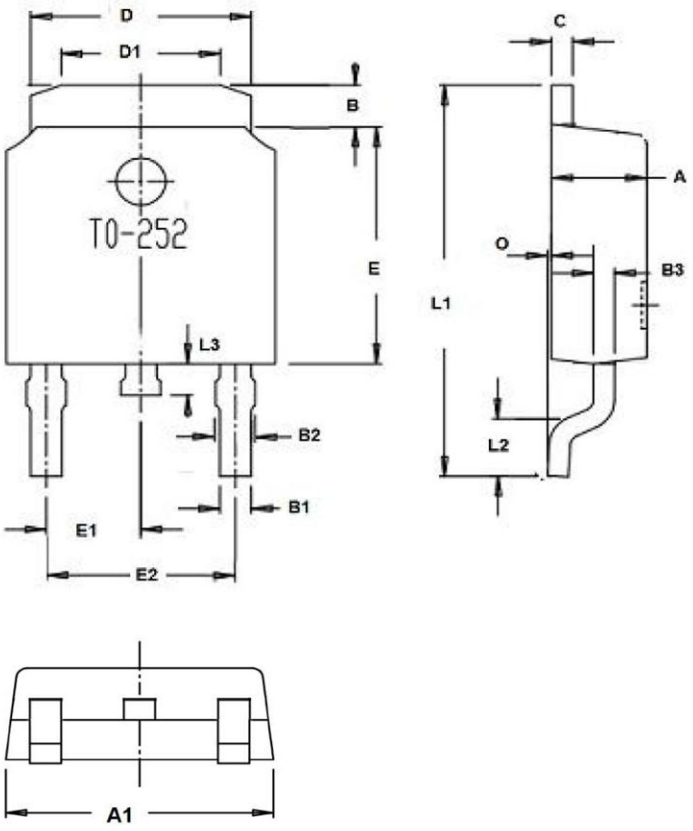


Figure 11. Gate Threshold Voltage vs. Junction Temperature

■ Package Information

TO-252



Dim.	Min.	Max.
A	2.1	2.5
A1	6.3	6.9
B	0.96	1.42
B1	0.74	0.86
B2	0.74	0.94
C	Typ0.5	
D	5.33	5.53
D1	3.65	4.05
E	6.0	6.2
E1	Typ2.29	
E2	Typ4.58	
O	0	0.15
L1	9.9	10.5
L2	Typ1.65	
L3	0.6	1.0
All Dimensions in millimeter		